

# Epson, Fujitsu Announce Results of Joint Project to Develop Next-Generation FRAM Technology

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Seiko Epson and Fujitsu today announced the results of their joint project to develop next-generation Ferroelectric Random Access Memory (FRAM) technology.

Since announcing a joint development agreement in June 2005, Epson and Fujitsu have collaborated on development of next-generation technology for FRAM non-volatile memory. The joint development project was successfully completed recently and produced the anticipated results.

Through the project, the two companies developed technology for forming, processing and evaluating a new ferroelectric (PZT) film and created FRAM memory core process technology that is highly integrated (four times the level of conventional FRAM), features high performance (read/write speeds over three times faster than conventional FRAM) and boasts outstanding reliability (capable of more than one hundred trillion read/write cycles).

FRAM is currently attracting attention as a cutting-edge technology for secure memory, and this level of performance is a world first. Since the ferroelectric process can be added to existing CMOS logic processes, it will be suitable for the development of mass production technologies.

Epson intends to combine the results of this joint project with its own

low power consumption CMOS technology to further speed up development and commercialization of integrated large-scale integrated circuits (LSIs) for applications such as battery-operated and portable devices.

Fujitsu will proceed with development of mass production technologies based on the results of this joint project. In addition to leveraging FRAM's advantages of low power consumption and high read/write speeds in the security applications market for which FRAM is suited for, Fujitsu will create new markets for embedded FRAM microcontrollers and accommodate diverse customer needs.

Source: Fujitsu

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